

P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING

DESCRIPTION

The μ PA1911 is a switching device which can be driven directly by a 2.5-V power source.

The μ PA1911 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 2.5-V power source
- Low on-state resistance

$R_{DS(on)1} = 115 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -1.5 \text{ A)}$

$R_{DS(on)2} = 120 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -1.5 \text{ A)}$

$R_{DS(on)3} = 190 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -1.0 \text{ A)}$

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1911TE	6-pin Mini Mold (Thin Type)

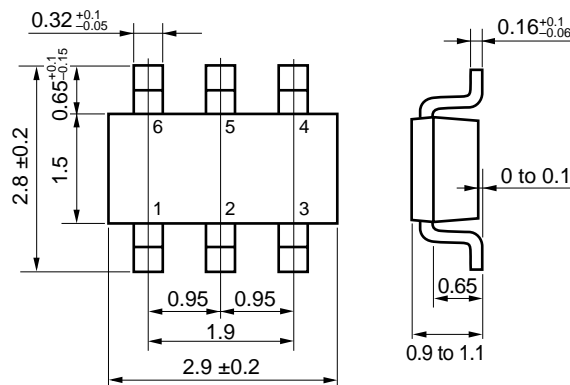
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	-20	V
Gate to Source Voltage	V_{GSS}	-12/+6	V
Drain Current (DC)	$I_{D(DC)}$	∓ 2.5	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	∓ 10	A
Total Power Dissipation	P_{T1}	0.2	W
Total Power Dissipation ^{Note2}	P_{T2}	2	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1 \%$
2. Mounted on FR-4 board, $t \leq 5 \text{ sec.}$

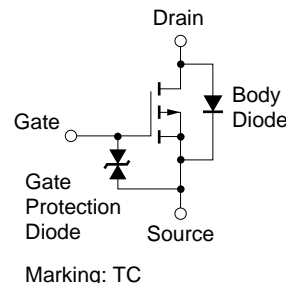
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit : mm)



- 1, 2, 5, 6 : Drain
3 : Gate
4 : Source

EQUIVALENT CIRCUIT

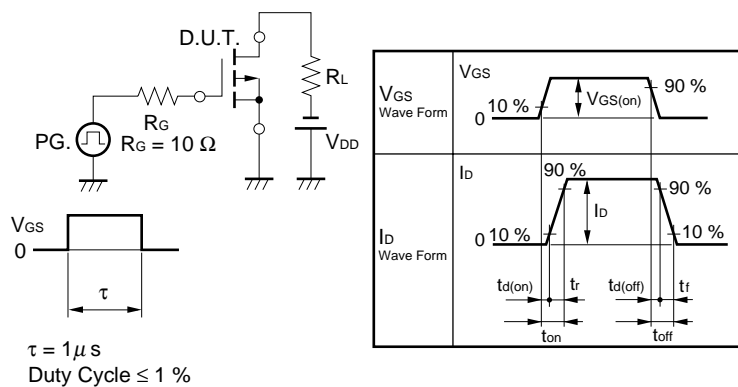


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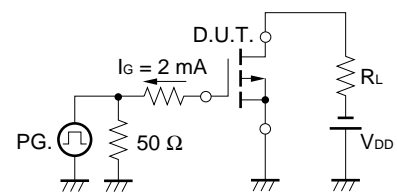
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-0.5	-0.92	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -1.5 A	1	4.5		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -1.5 A		80	115	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -1.5 A		86	120	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -1.0 A		130	190	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		540		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		190		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		90		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V		140		ns
Rise Time	t _r	I _D = -1.5 A		500		ns
Turn-off Delay Time	t _{d(off)}	V _{GS(on)} = -4.0 V		420		ns
Fall Time	t _f	R _G = 10 Ω		850		ns
Total Gate Charge	Q _G	V _{DD} = -10 V		5.0		nC
Gate to Source Charge	Q _{GS}	I _D = -2.5 A		1.5		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = -4.0 V		2.0		nC
Diode Forward Voltage	V _{F(S-D)}	I _F = 2.5 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	t _{rr}	I _F = 2.5 A, V _{GS} = 0 V		30		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 10 A/μs		2.0		nC

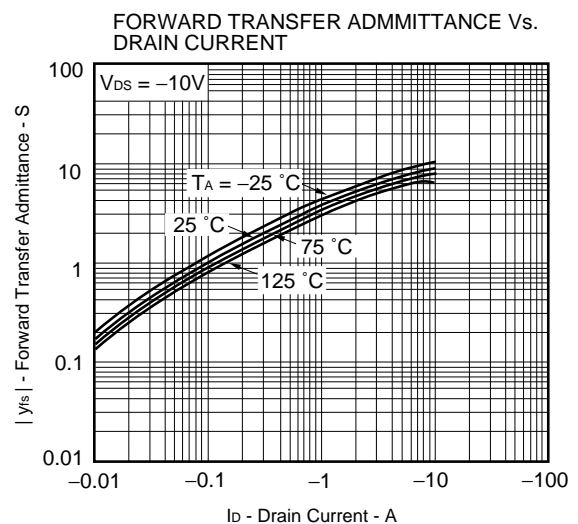
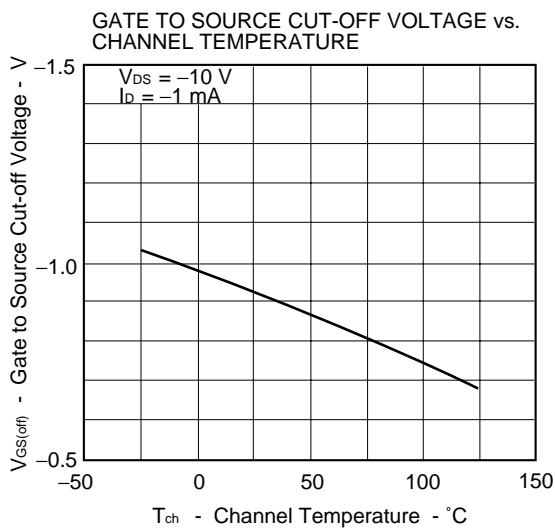
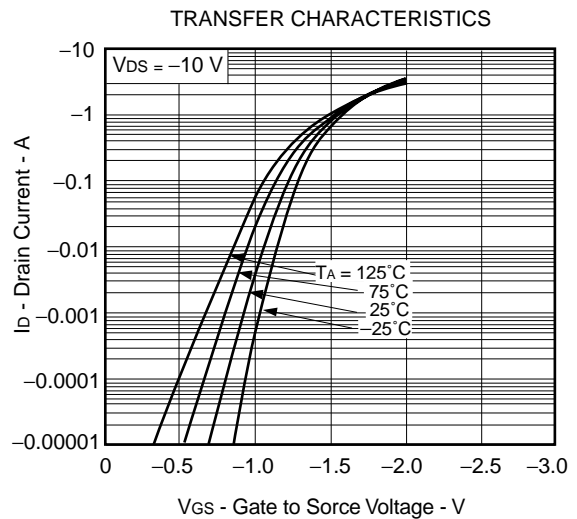
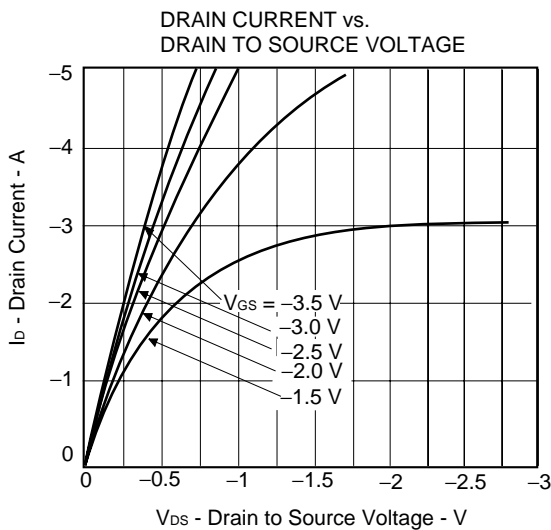
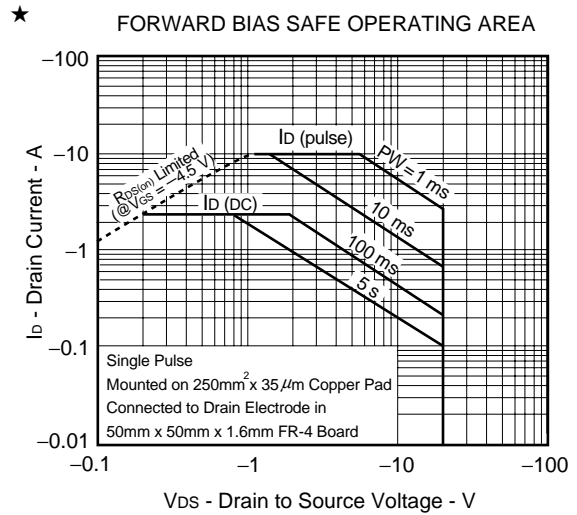
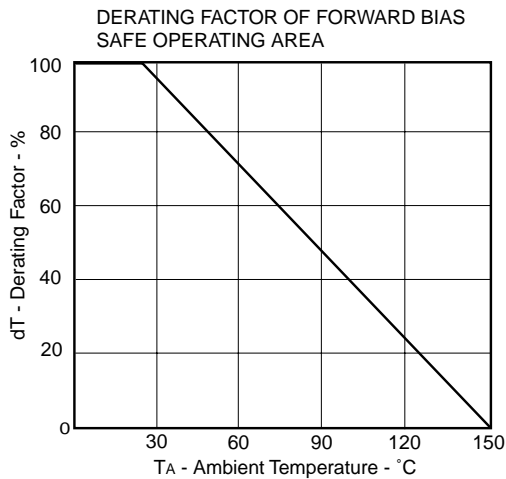
TEST CIRCUIT 1 SWITCHING TIME

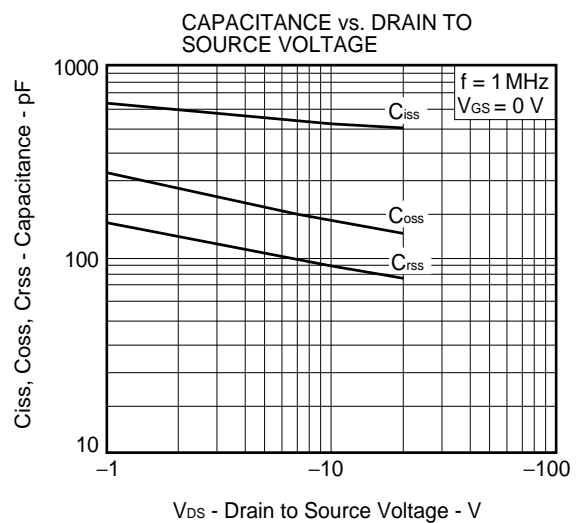
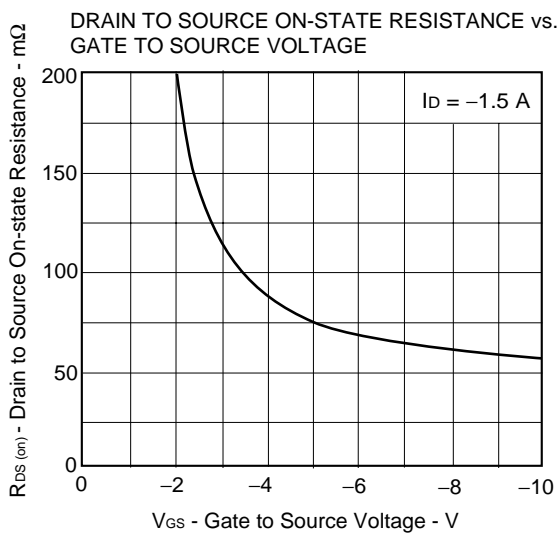
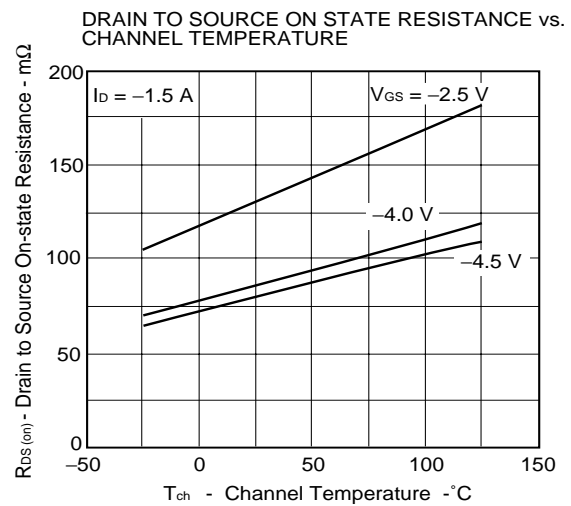
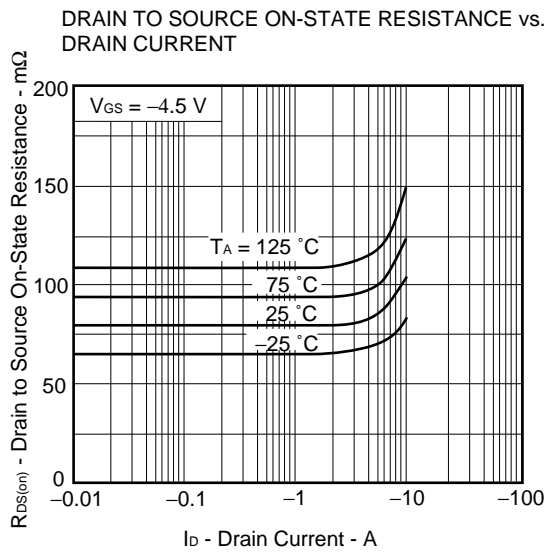
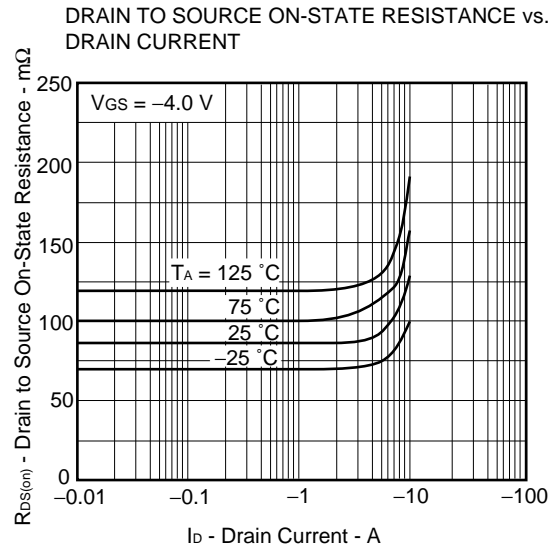
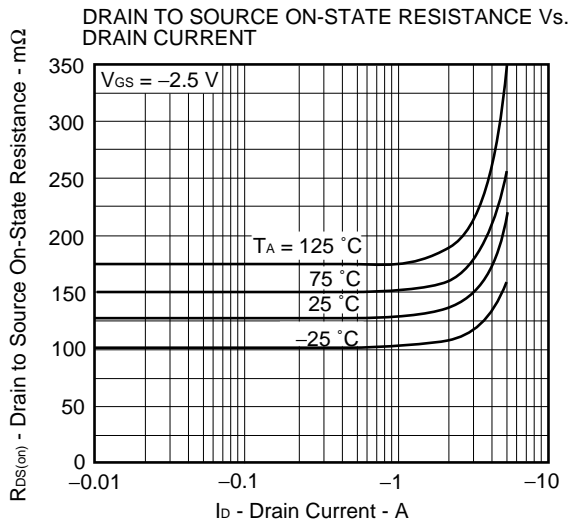


TEST CIRCUIT 2 GATE CHARGE

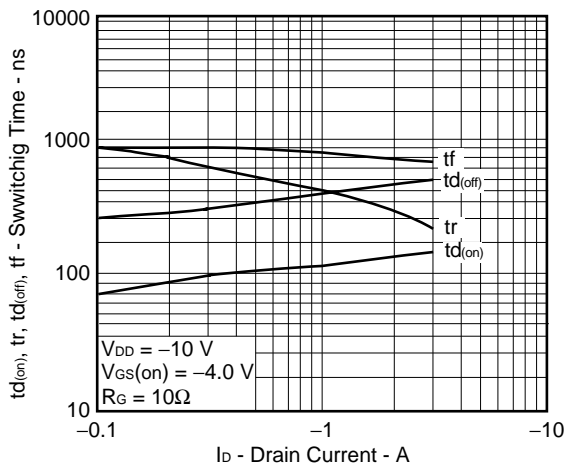


TYPICAL CHARACTERISTICS (TA = 25°C)

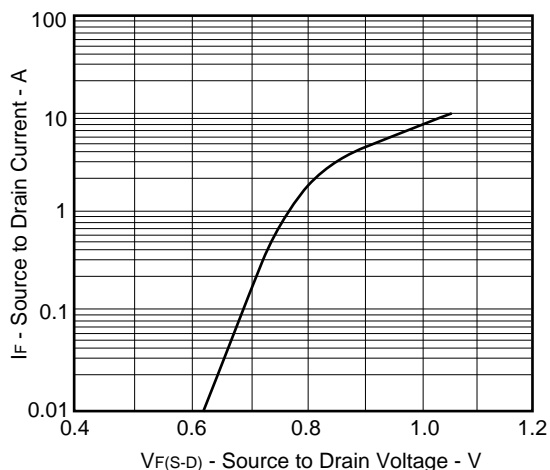




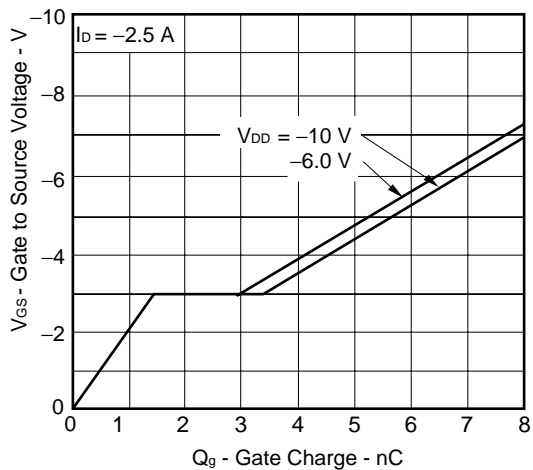
SWITCHING CHARACTERISTICS



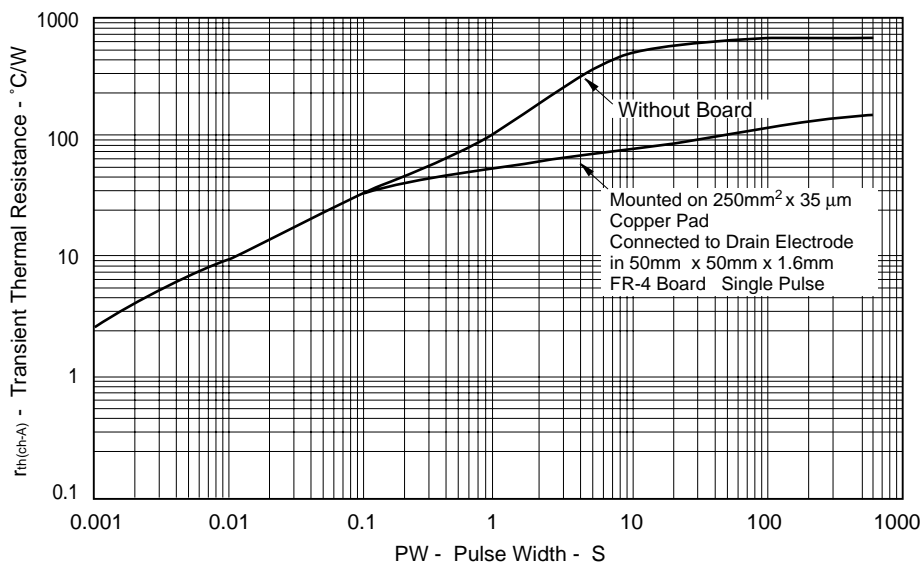
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



★ TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



[MEMO]

[MEMO]

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